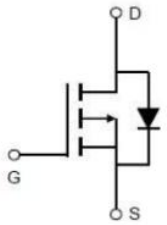
AP85P20G

P-Channel Enhancement Mosfet

DATA SHEET

Features

- -20V,-85A
  $R_{DS(ON)}$ <3.0mΩ @V_{GS}=-4.5V TYP: 2.1mΩ
  $R_{DS(ON)}$ <3.8mΩ @V_{GS}=-2.5V TYP: 3.1mΩ
  $R_{DS(ON)}$ <5.6mΩ @V_{GS}=-1.8V TYP: 5.1mΩ
- Advanced Trench Technology
- Lead free product is acquired
- Excellent $R_{DS(ON)}$ and Low Gate Charge



Schematic Diagram

Applications

- Load switching
- PWM Application
- Power Management



Marking and pin Assignment

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity (PCS)
85P20G	AP85P20G	PDFN5X6	-	-	5000

ABSOLUTE MAXIMUM RATINGS (T_J=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	±12	V
Continuous Drain Current (Tc=25℃) (1)	I_D	-85	A
Continuous Drain Current (Tc=100℃)	I_D	-54	A
Pulsed Drain Current (1)	I_{DM}	-340	A
Drain Power Dissipation	P_D	125	W
Single Pulsed Avalanche Energy (2)	E_{AS}	150	mJ
Thermal Resistance from Junction to Ambient (3)	$R_{\theta JA}$	43	℃/W
Thermal Resistance from Junction to Case	$R_{\theta JC}$	1.0	℃/W
Junction Temperature	T_J	-55~ +150	℃
Storage Temperature	T_{STG}	-55~ +150	℃

Notes:

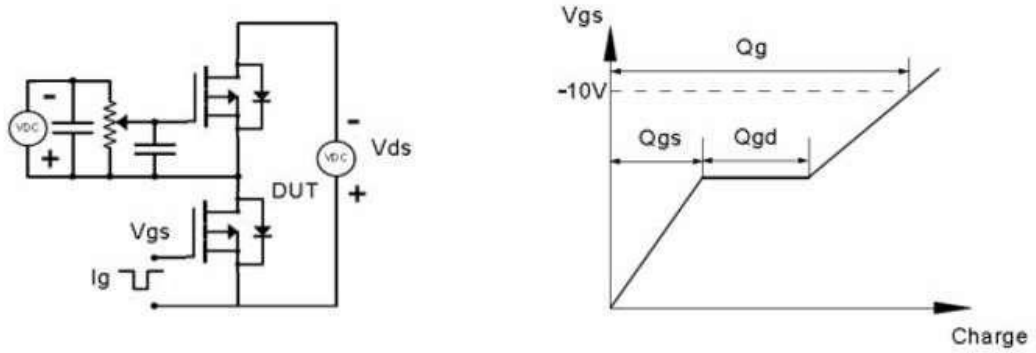
1) Repetitive Rating: pulse width limited by maximum junction temperature
2) EAS condition : T_J=25℃, V_{DD}=-10V, V_G=-10V, L=0.5mH, R_g=25Ω, I_{AS}=-24.5A
3) The value of RθJA Mounted on FR4 Board（25.4mm*25.4mm*t1.6mm）With 2oz Copper TA=25℃

MOSFET ELECTRICAL CHARACTERISTICS(T_J=25℃ unless otherwise noted)

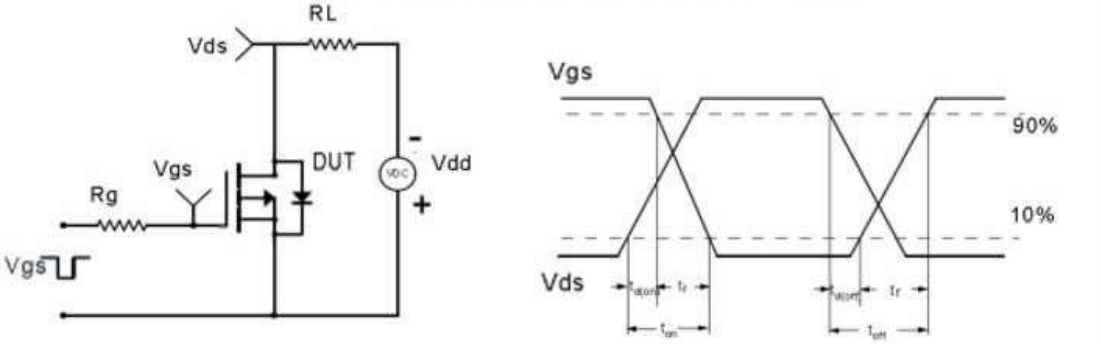
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D =-250μA	-20	-	-	V
Zero gate voltage drain current	I_{DSS}	V_{DS} =-20V, V_{GS} = 0V	-	-	-1	μA
Gate-body leakage current	I_{GSS}	V_{GS} =±12V, V_{DS} = 0V	-	-	±100	nA
Gate threshold voltage	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D =-250μA	-0.4	-0.7	-1.0	V
Drain-source on-resistance	$R_{DS(on)}$	V_{GS} =-4.5V, I_D =-30A	-	2.1	3.0	mΩ
		V_{GS} =-2.5V, I_D =-20A	-	3.1	3.8	
		V_{GS} =-1.8V, I_D =-15A	-	5.1	5.6	
Forward transconductance	R_g	V_{GS}= 0V, V_{DS}= 0V, f=1.0MHz	-	5.3	-	Ω
Dynamic characteristics						
Input Capacitance	C_{iss}	V_{DS} =-10V, VGS=0V, f=1MHz	-	10500	-	pF
Output Capacitance	C_{oss}		-	1300	-	
Reverse Transfer Capacitance	C_{rss}		-	888	-	
Switching characteristics						
Turn-on delay time	$t_{d(on)}$	V_{DD}=-10V, I_D=-30A, R_G=3Ω, V_{GS}=-4.5V	-	16	-	ns
Turn-on rise time	t_r		-	50	-	
Turn-off delay time	$t_{d(off)}$		-	249	-	
Turn-off fall time	t_f		-	128	-	
Total Gate Charge	Qg	V_{DS}=-10V, I_D=-30A, V_{GS}=-4.5V	-	95	-	nC
Gate-Source Charge	Qgs		-	17	-	
Gate-Drain Charge	Qgd		-	20	-	
Source-Drain Diode characteristics						
Diode Forward voltage	V_{SD}	T_J=25℃, V_{GS} =0V, I_S=-30A	-	-0.8	-1.2	V
Diode Forward current	I_S	T_C=25℃	-	-	-85	A
Body Diode Reverse Recovery Time	trr	T_J=25℃, I_F=-20A,di/dt=100A/us	-	36	-	ns
Body Diode Reverse Recovery Charge	Qrr		-	28	-	nC

Test Circuit & Waveform

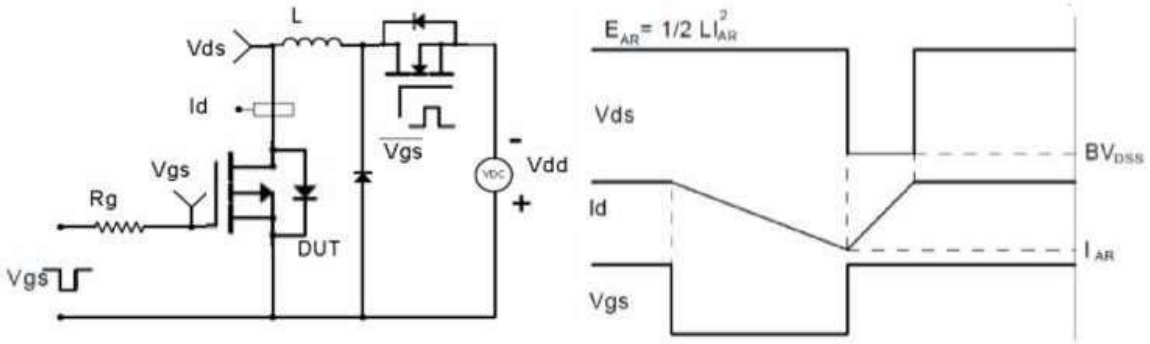
Gate Charge Test Circuit & Waveform



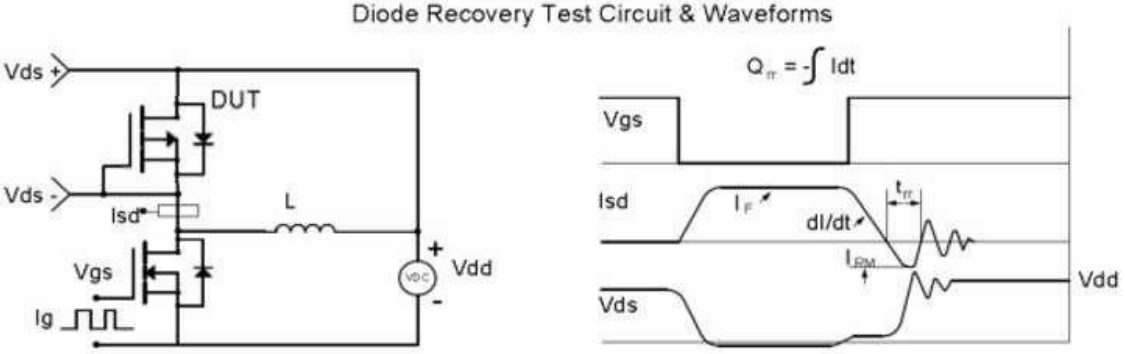
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Typical Characteristics

Figure 1: Output Characteristics

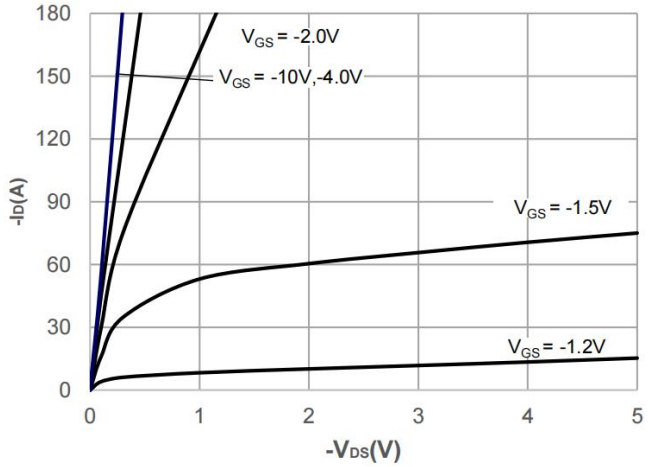


Figure 2: Typical Transfer Characteristics

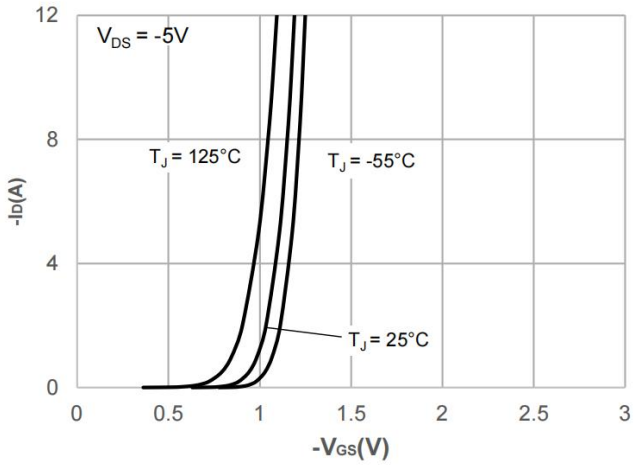


Figure 3: Power De-rating

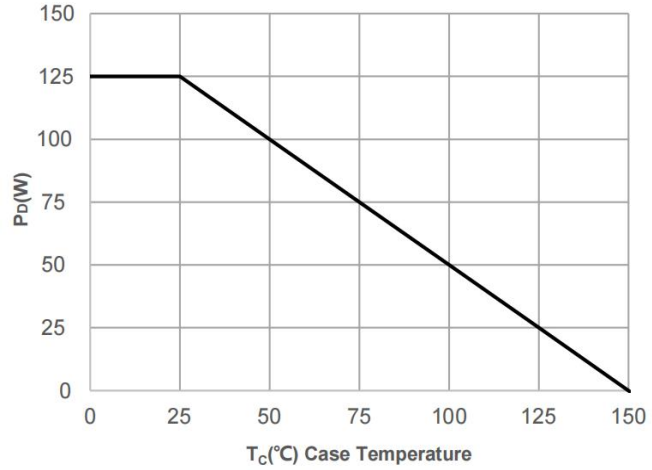


Figure 4: Current De-rating

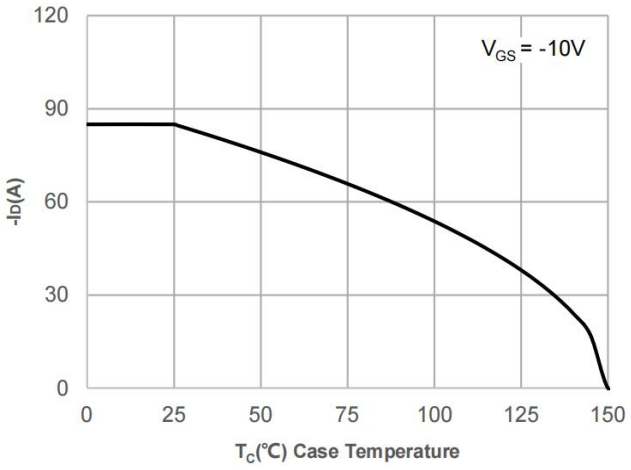


Figure 5: On-resistance vs. Drain Current

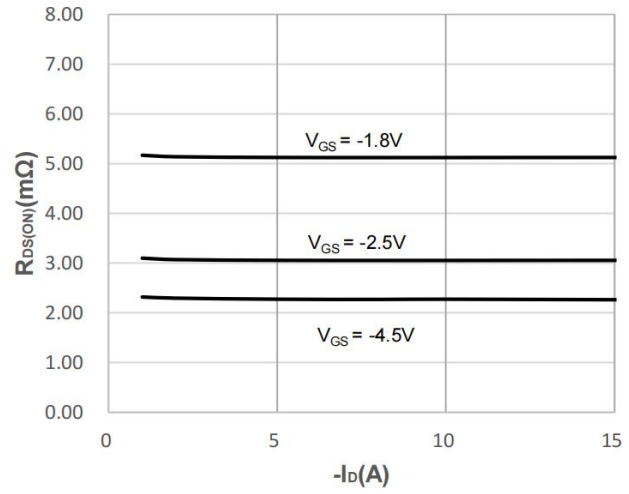
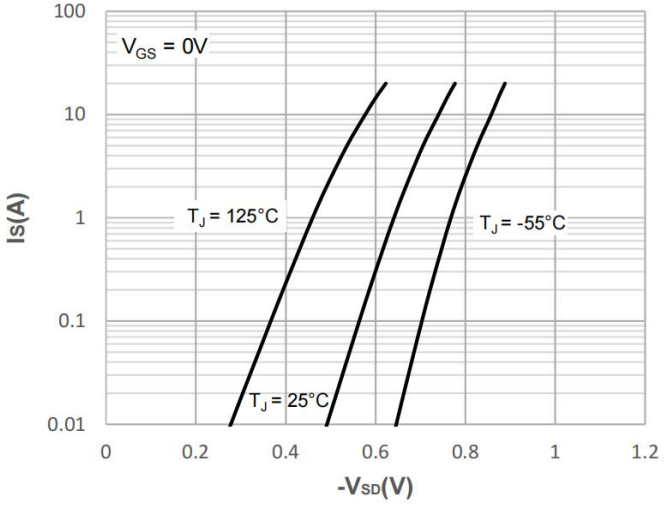


Figure 6: Body Diode Characteristics



Typical Characteristics

Figure 7: Normalized Breakdown voltage vs. Junction Temperature

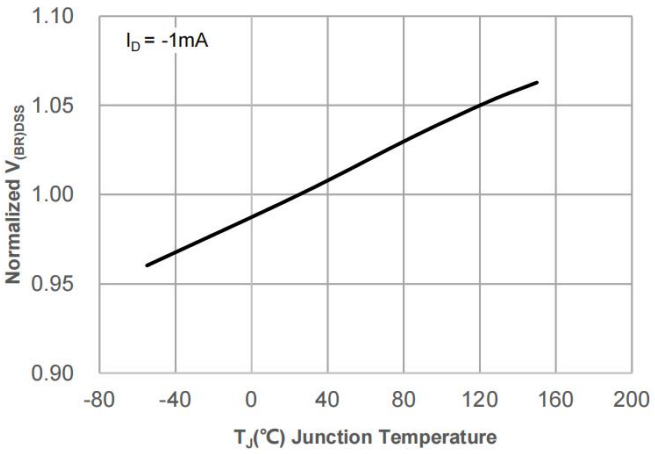


Figure 8: Normalized Threshold Voltage vs. Junction Temperature

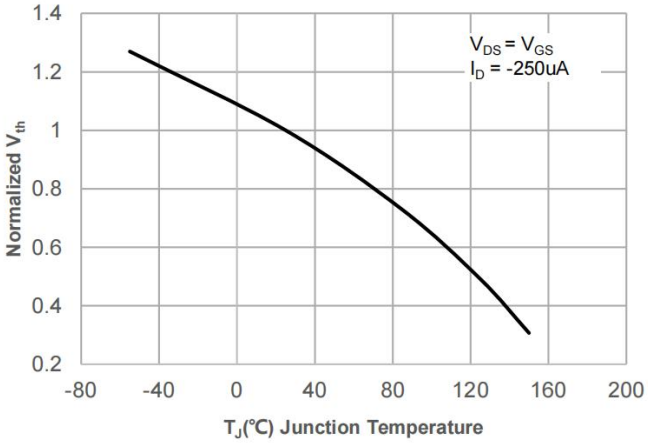


Figure 9: Gate Charge Characteristics

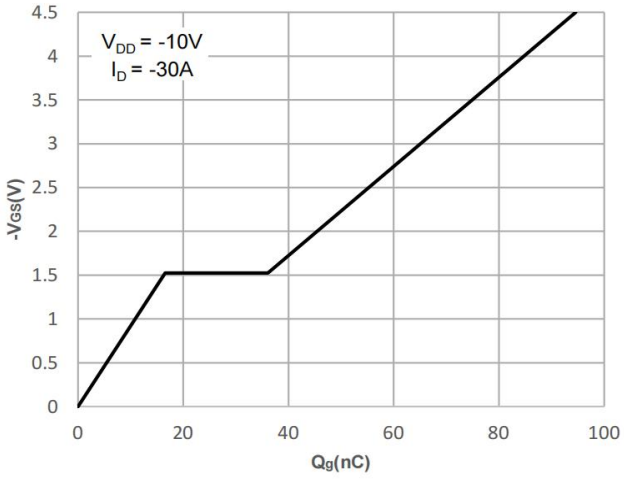


Figure 10: Capacitance Characteristics

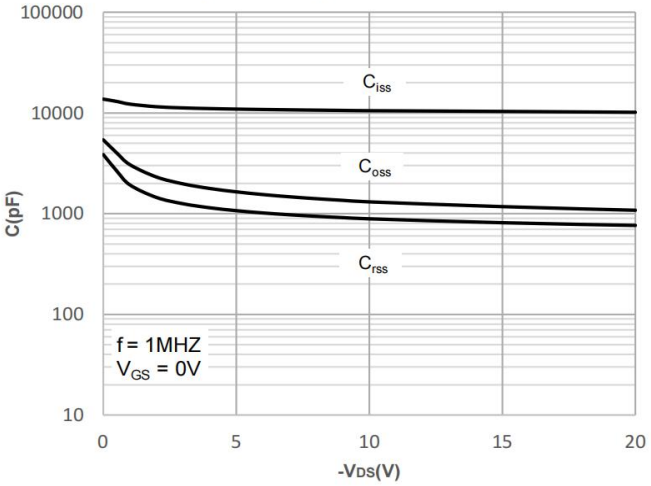


Figure 11: $R_{DS(ON)}$ vs. V_{GS}

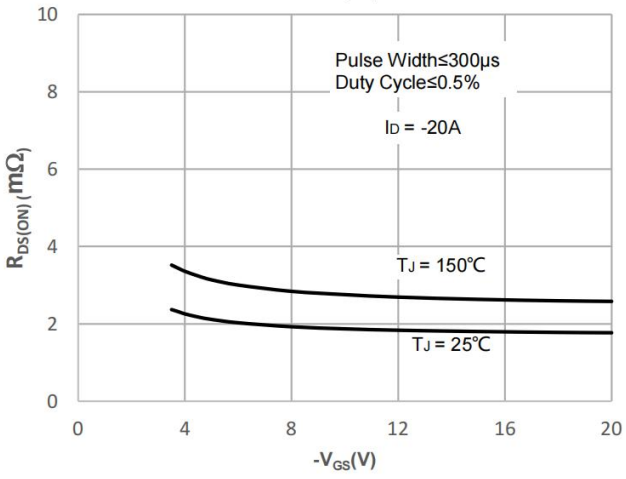
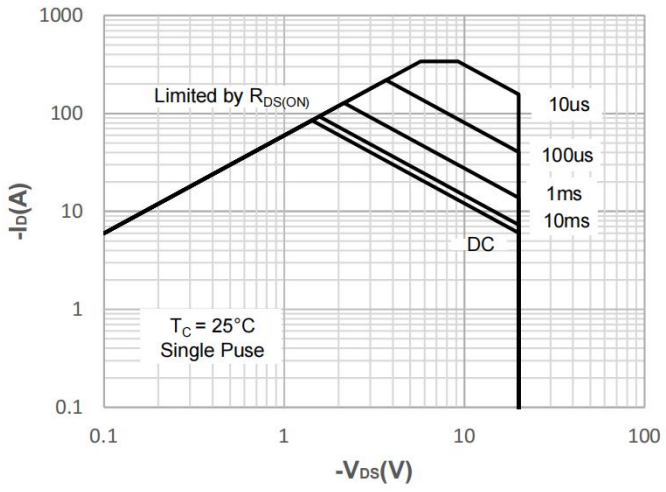
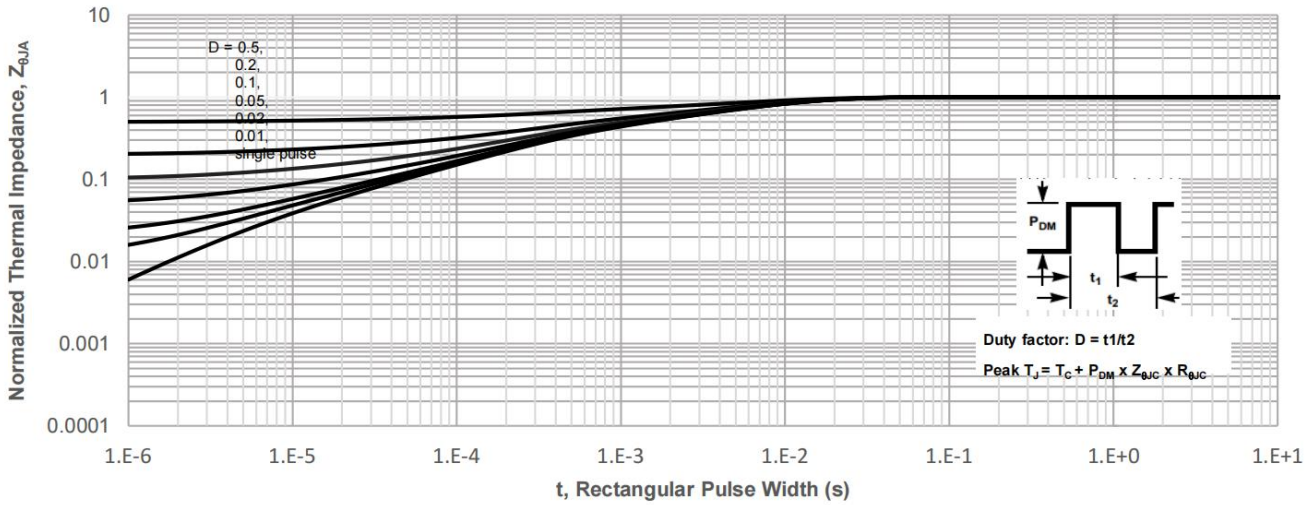


Figure 12: Maximum Safe Operating Area

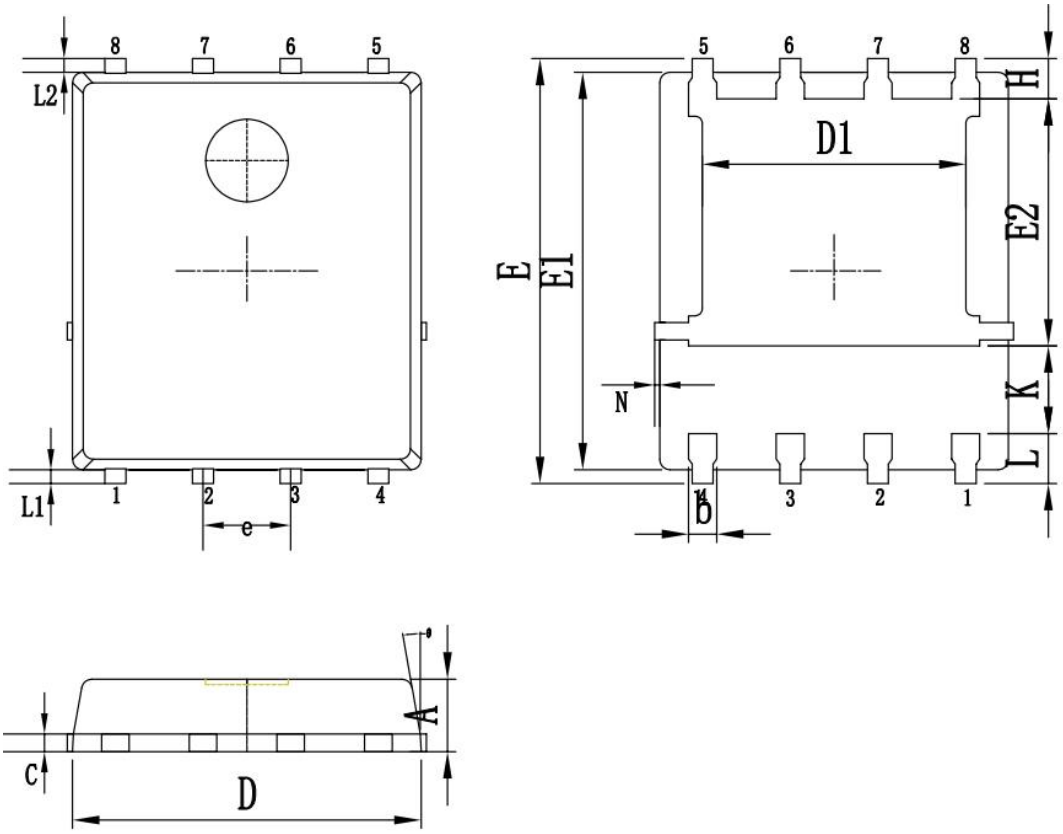


Typical Characteristics

Figure 13: Normalized Maximum Transient Thermal Impedance



PDFN5X6 Package Information



Symbols	Millimeters		
	MIN.	NOM.	MAX.
A	0.90	1.05	1.20
b	0.20	0.40	0.50
C	0.20	0.25	0.35
D	4.80	5.05	5.20
D1	3.80	3.90	4.10
E	5.90	6.00	6.20
E1	5.60	5.75	5.90
E2	3.40	3.50	3.60
e	1.27 BSC.		
H	0.40	0.60	0.70
K	1.17	1.27	1.37
L	0.50	0.74	0.84
L1/L2	0.10	0.16	0.20
θ	8°	10°	12°
N	0	-	0.15

Revision History

Revision	Release	Remark
V1.0	2024/10/11	Initial Release
V1.1	2024/11/21	Update $R_{DS(on)}$ Type Value

Disclaimer

The information given in this document describes the independent performance of the product,but similar performance is not guaranteed under other working conditions,and cannot be guaranteed when installed with other products or equipment.To achieve the required performance of the product in actual scenarios,the customer should conduct a complete application test to assess the functionality of the product.

Allpower assumes no responsibility for equipment failures result from using products at values that exceed the ratings,operating conditions,or other parameters listed in the product specifications.

The product described in this specification is not applicable for aerospace or other applications which
requires high reliability.Customers using or selling these products for use in medical,life-saving,or life-sustaining applications do so at their own risk and agree to fully indemnify.

Due to product or technical improvements,the information described or contained herein may be changed without prior notice.